

SANYO	No.1791C	2SK543
		N-Channel MOS Silicon FET FM Tuner, VHF-Band Amp Applications

Features

- . Low noise. NF=1.8dB typ(f=100MHz)
- . High power gain. PG=27dB typ(f=100MHz)
- . Small reverse transfer capacitance. $c_{rss}=0.035\text{pF}(V_{DS}=10\text{V}, f=1\text{MHz})$

Absolute Maximum Ratings at Ta=25°C

			unit
Drain to Source Voltage	V_{DS}	20	V
Gate to Source Voltage	V_{GS}	±5	V
Drain Current	I_D	30	mA
Allowable Power Dissipation	P_D	200	mW
Channel Temperature	T_{ch}	125	°C
Storage Temperature	T_{stg}	-55 to +125	°C

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Drain to Source Voltage	V_{DSX}	$V_{GS}=-4\text{V}, I_D=100\mu\text{A}$	20			V
Common Source Gate Cutoff Current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 5\text{V}$			10	nA
Drain Current	I_{DSS}	$V_{DS}=10\text{V}, V_{GS}=0\text{V}$	1.2*		12*	mA
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}, I_D=100\mu\text{A}$			-2.5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}, V_{GS}=0\text{V}$ f=1kHz		11		mS
Input Capacitance	c_{iss}	$V_{DS}=10\text{V}, V_{GS}=0\text{V}$ f=1MHz		2.4		pF
Reverse Transfer Capacitance	c_{rss}	$V_{DS}=10\text{V}, V_{GS}=0\text{V}$ f=1MHz		0.035		pF
Power Gain	PG	$V_{DS}=10\text{V}, V_{GS}=0\text{V}$ f=100MHz		27		dB
Noise Figure	NF	$V_{DS}=10\text{V}, V_{GS}=0\text{V}$ f=100MHz		1.8	3.0	dB

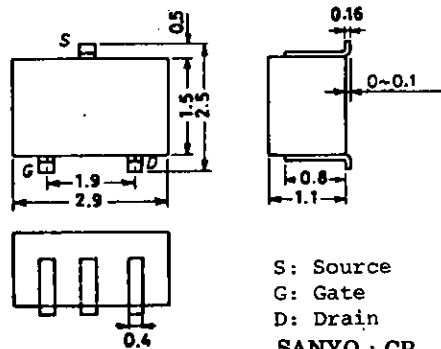
See specified Test Circuit.

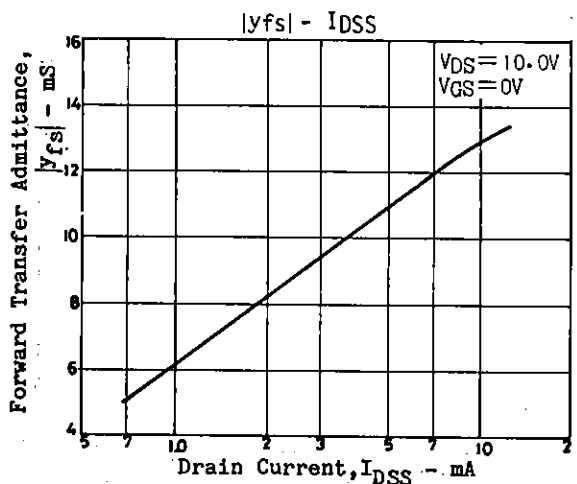
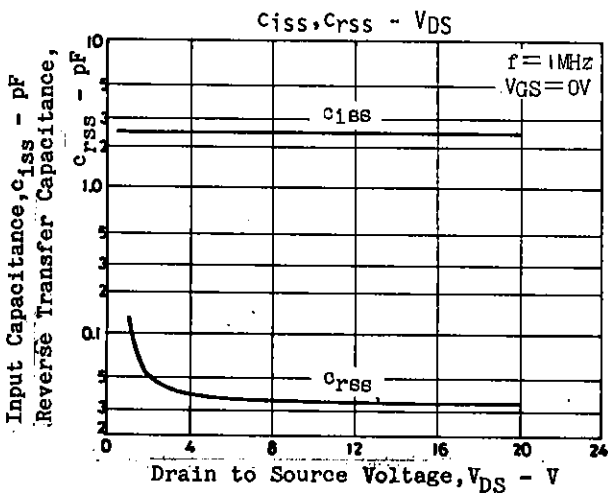
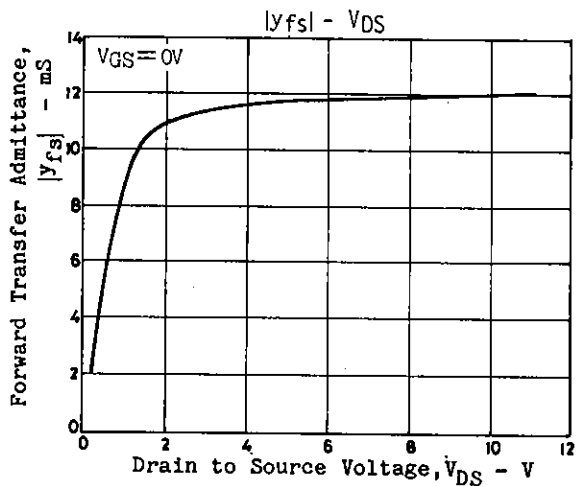
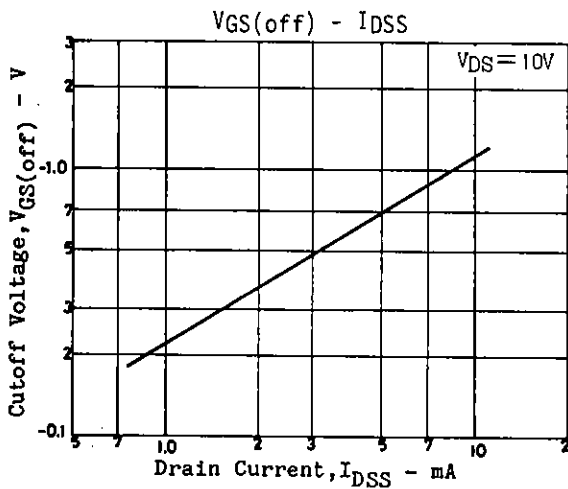
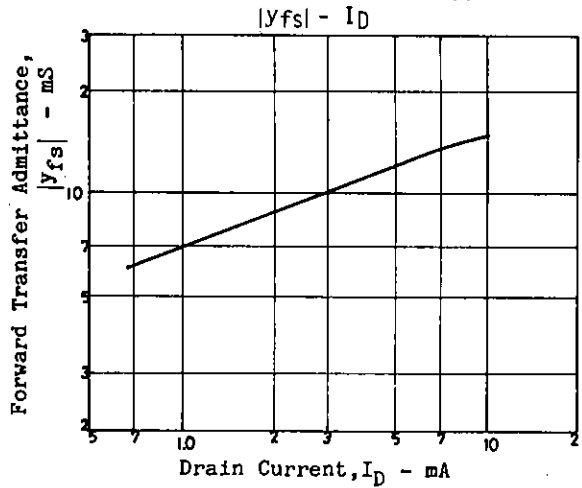
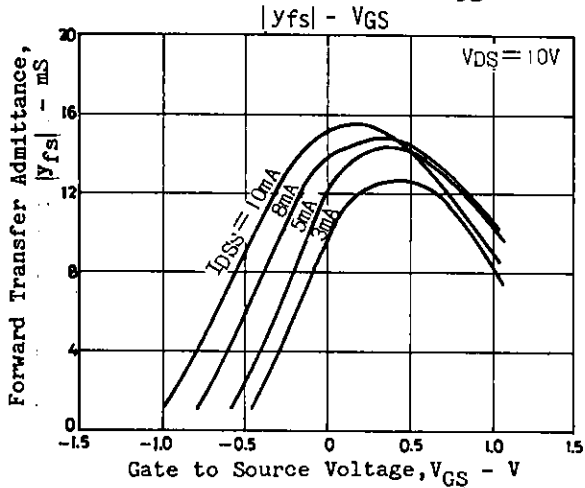
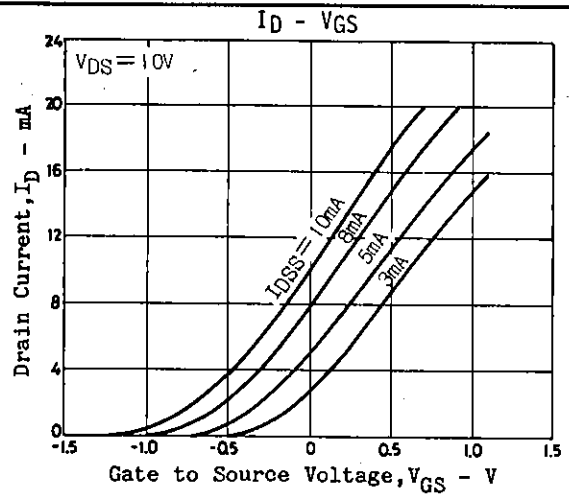
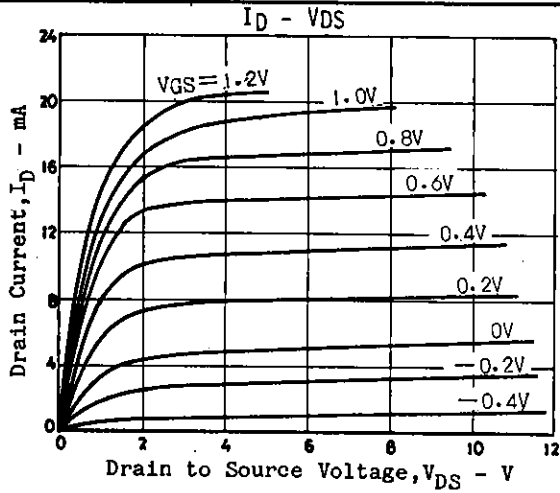
*: The 2SK543 is classified by I_{DSS} as follows (unit:mA):

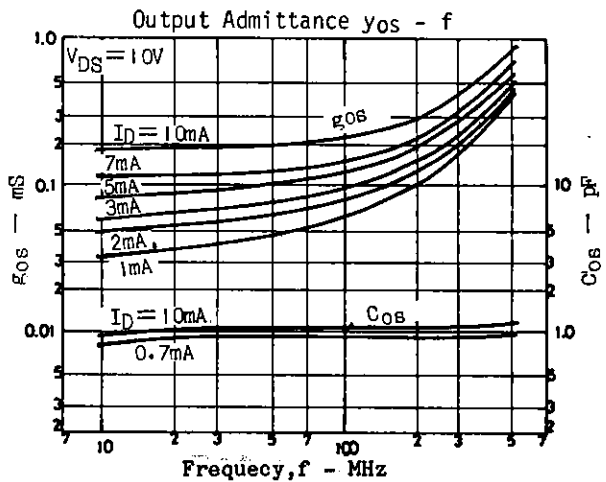
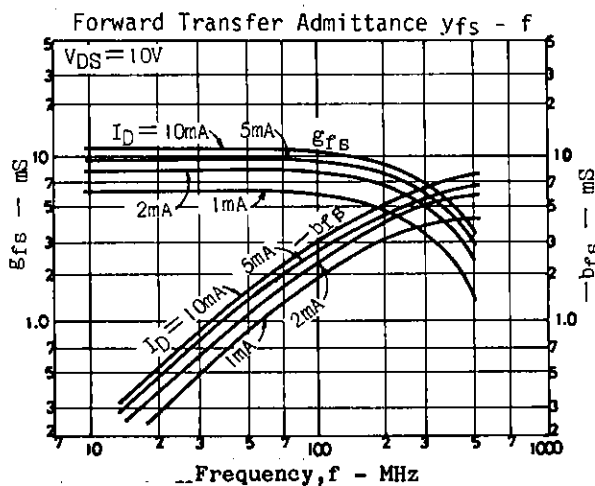
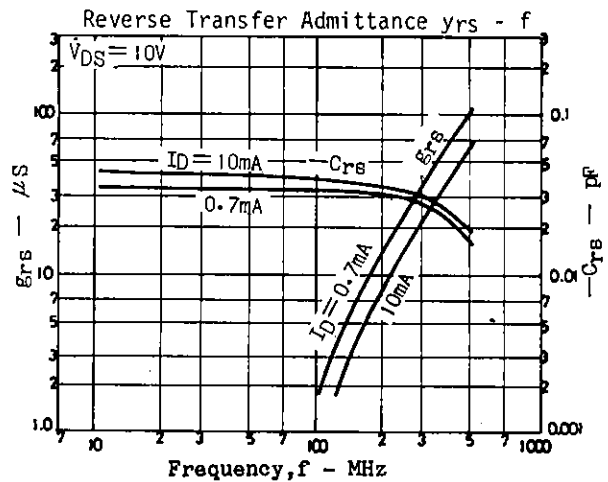
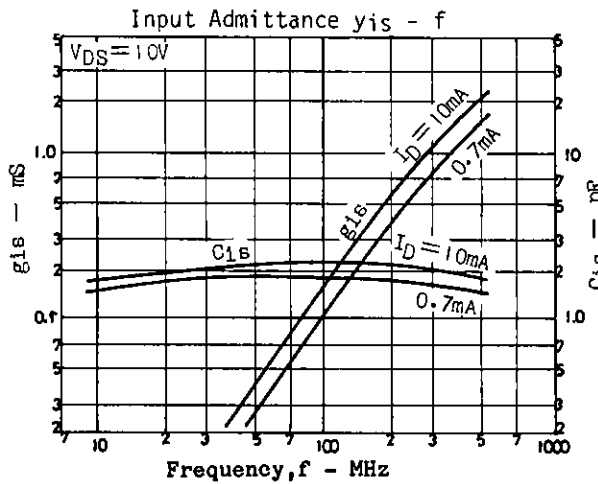
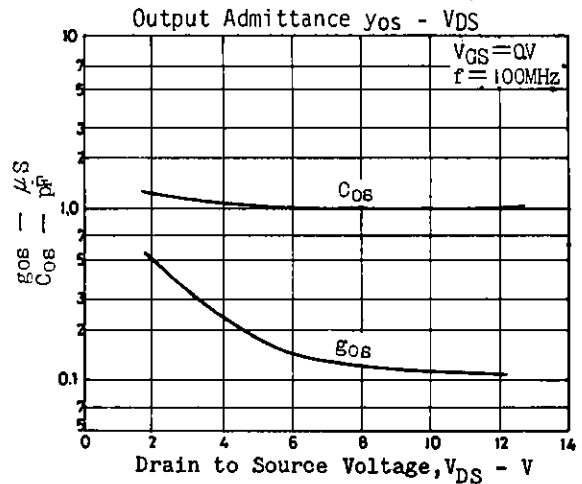
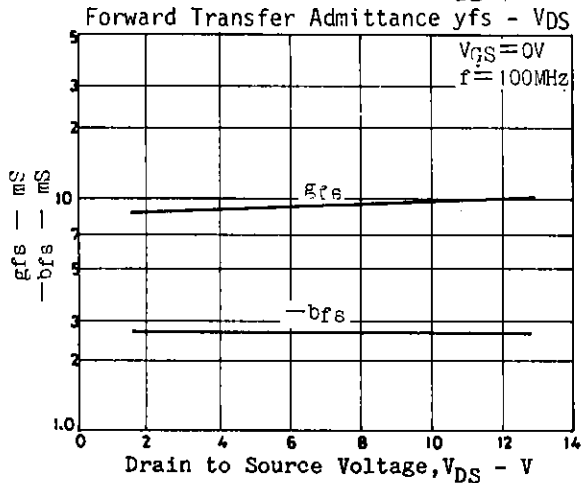
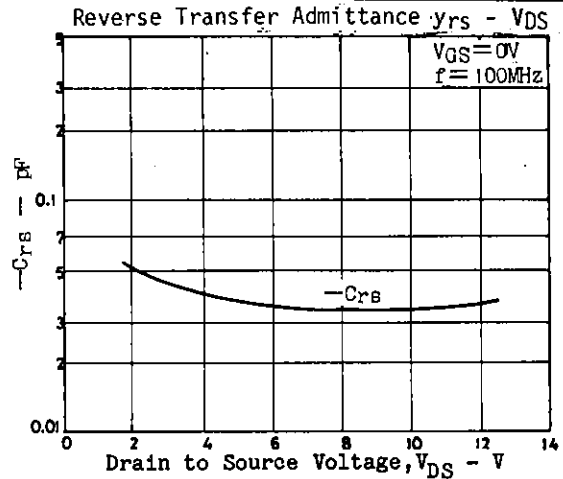
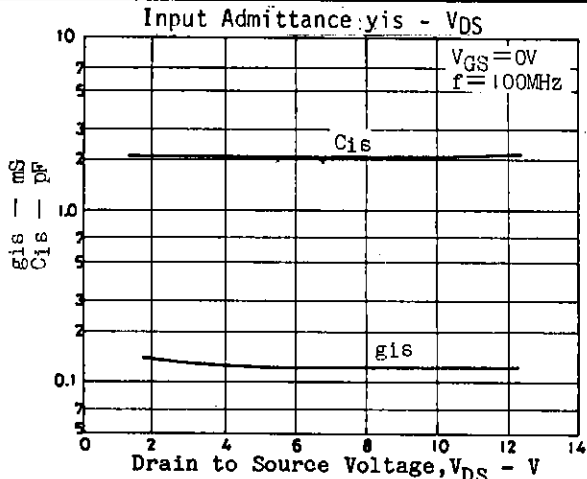
1.2	3	3.0	2.5	4	6.0	5.0	5	12
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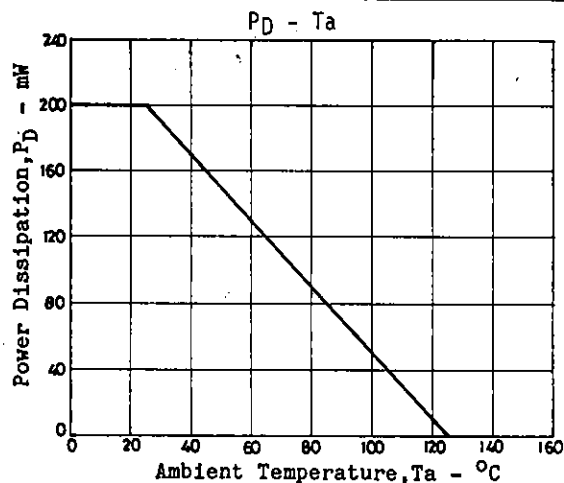
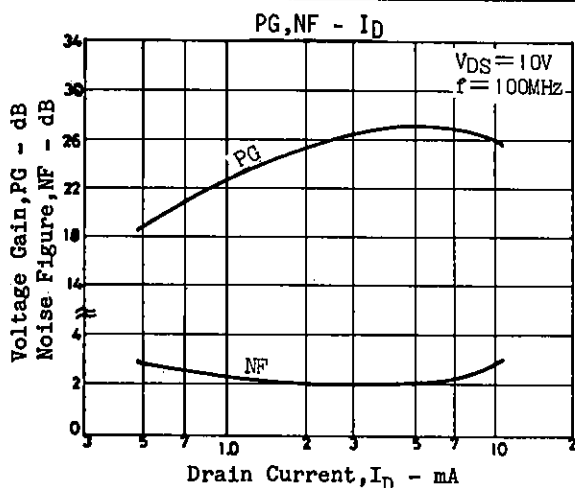
(Note) Marking :CJ
 I_{DSS} rank: 3,4,5

Package Dimensions 2024A
(unit:mm)

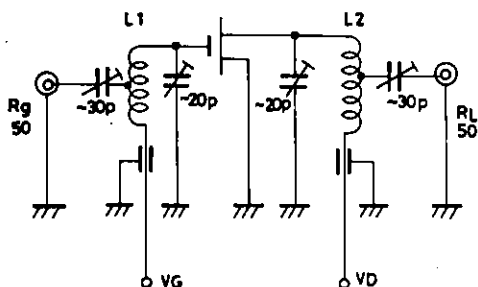








PG, NF Test Circuit



- L1: 1mm ϕ plated wire 10mm ϕ 6T, tap: 3T from H side
- L2: 1mm ϕ plated wire 10mm ϕ 7T, tap: 4T from H side

Unit (Resistance : Ω , Capacitance : F)

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